**Product data sheet** 

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

#### 2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate in four quadrants

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

### 4. Quick reference data

Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions  |  | Min | Тур | Max  | Unit |
|---------------------|--|---|--|-----|-----|------|------|
| $V_{DRM}$           | repetitive peak off-<br>state voltage    |   |  | -   | -   | 600  | V    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 |  | -   | -   | 12.5 | Α    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3                        |  | -   | -   | 1    | Α    |
| Static characte     | Static characteristics                   |   |  |     |     |      |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 9$       |  | 0.2 | -   | 3    | mA   |





**4Q Triac** 

| Symbol | Parameter | Conditions  | Min | Тур | Max | Unit |
|--------|-----------|---|-----|-----|-----|------|
|        |           | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$<br>$T_j = 25 \text{ °C; } Fig. 9$ | 0.2 | -   | 3   | mA   |
|        |           | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$<br>$T_j = 25 \text{ °C; } Fig. 9$           | 0.2 | -   | 3   | mA   |
|        |           | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$<br>$T_j = 25 \text{ °C; } Fig. 9$   | 0.2 | -   | 5   | mA   |

# 5. Pinning information

### Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline         | Graphic symbol |
|-----|--------|-----------------|----------------------------|----------------|
| 1   | T1     | main terminal 1 | 4                          | T2—T1          |
| 2   | T2     | main terminal 2 |                            | Sym051         |
| 3   | G      | gate            |                            | <b>.</b>       |
| 4   | T2     | main terminal 2 | ☐1 ☐2 ☐3<br>SC-73 (SOT223) |                |

# 6. Ordering information

### Table 3. Ordering information

| Type number | Package |  |         |
|-------------|---------|--|---------|
|             | Name    | Description  | Version |
| Z0103MN0    | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

# 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| Z0103MN0    | 103MN0       |

**4Q Triac** 

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min | Max  | Unit             |
|---------------------|--------------------------------------|---|-----|------|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   | -   | 600  | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | full sine wave; $T_{sp} \le 105 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3                        | -   | 1    | A                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5 | -   | 12.5 | A                |
|                     |                                      | full sine wave; $T_{j(init)} = 25 \text{ °C}$ ;<br>$t_p = 16.7 \text{ ms}$                | -   | 13.8 | A                |
| I <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t <sub>p</sub> = 10 ms; SIN   | -   | 0.78 | A <sup>2</sup> s |
| dl <sub>T</sub> /dt | rate of rise of on-state current     | $I_T$ = 1 A; $I_G$ = 20 mA; $dI_G/dt$ = 100 mA/ $\mu$ s; T2+ G+                           | -   | 50   | A/µs             |
|                     |                                      | $I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$<br>$\mu$ s; T2+ G-    | -   | 50   | A/µs             |
|                     |                                      | $I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$<br>$\mu$ s; T2- G-    | -   | 50   | A/µs             |
|                     |                                      | $I_T = 1 \text{ A}; I_G = 20 \text{ mA}; dI_G/dt = 100 \text{ mA/}$<br>$\mu$ s; T2- G+    | -   | 20   | A/µs             |
| I <sub>GM</sub>     | peak gate current                    |   | -   | 1    | Α                |
| $P_{GM}$            | peak gate power                      |   | -   | 2    | W                |
| P <sub>G(AV)</sub>  | average gate power                   | over any 20 ms period   | -   | 0.1  | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40 | 150  | °C               |
| Tj                  | junction temperature                 |   | -   | 125  | °C               |

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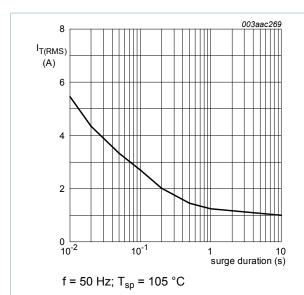


Fig. 1. RMS on-state current as a function of surge duration; maximum values

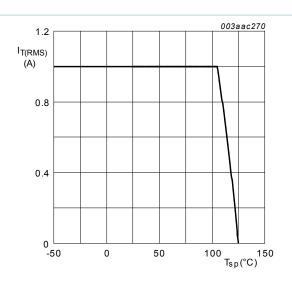
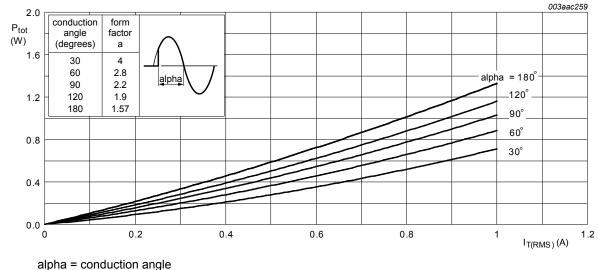


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

4/15

**4Q Triac** 

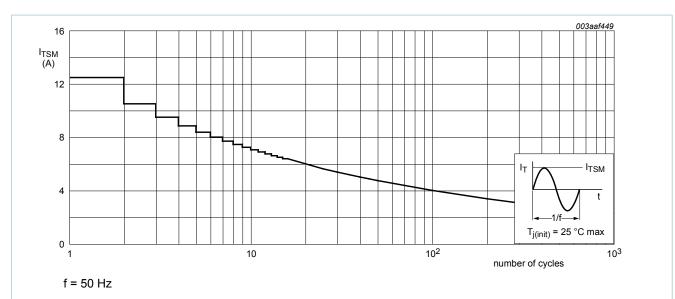


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

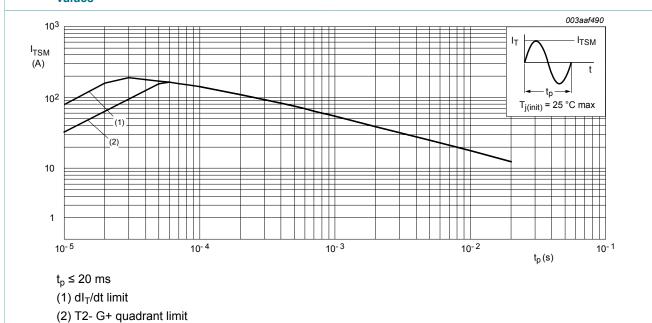


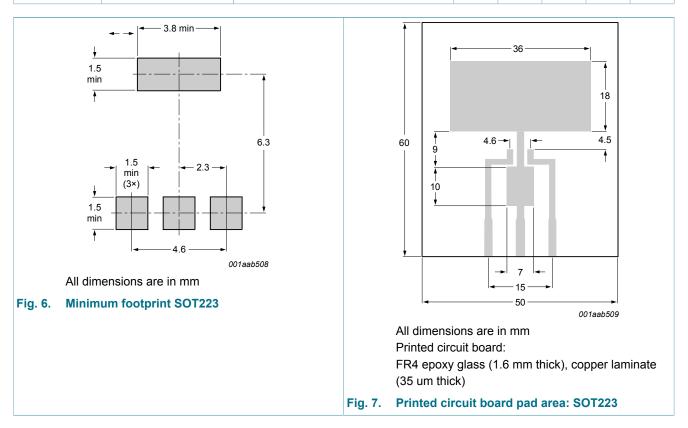
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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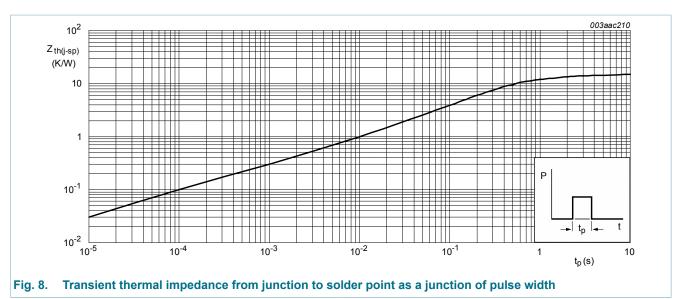
## **Thermal characteristics**

Table 6. **Thermal characteristics** 

| Symbol                | Parameter  | Conditions  | Min | Тур | Max | Unit |
|-----------------------|--|---|-----|-----|-----|------|
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point | full cycle; Fig. 8  | -   | -   | 15  | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient      | in free air; printed-circuit board<br>mounted: minimum footprint; full cycle;<br>Fig. 6 | -   | 156 | -   | K/W  |
|                       |  | in free air; printed-circuit board mounted: pad area; full cycle; Fig. 7                | -   | 70  | -   | K/W  |



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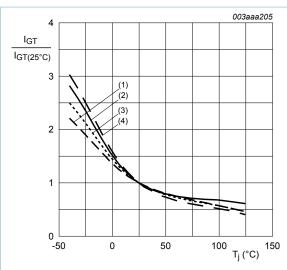
**4Q Triac** 

# 10. Characteristics

Table 7. Characteristics

| Symbol                | Parameter                             | Conditions   | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|-----|-----|-----|------|
| Static chara          | acteristics                           |  |     |     |     |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 9$                                  | 0.2 | -   | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; Fig. 9$                          | 0.2 | -   | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 9}}$ | 0.2 | -   | 3   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 ^{\circ}\text{C}; \text{ Fig. 9}$            | 0.2 | -   | 5   | mA   |
| L                     | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 10$                                 | -   | -   | 7   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$<br>$T_j = 25 \text{ °C}; Fig. 10$                         | -   | -   | 20  | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$<br>$T_j = 25 \text{ °C}; Fig. 10$                         | -   | -   | 7   | mA   |
|                       |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$<br>$T_j = 25 \text{ °C}; Fig. 10$                         | -   | -   | 7   | mA   |
| Н                     | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>  | -   | -   | 7   | mA   |
| / <sub>T</sub>        | on-state voltage                      | I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>   | -   | 1.3 | 1.6 | V    |
| / <sub>GT</sub>       | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 13   | -   | -   | 1   | V    |
|                       |                                       | $V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 °C;$<br>Fig. 13   | 0.2 | -   | -   | V    |
| D                     | off-state current                     | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -   | -   | 0.5 | mA   |
| Oynamic ch            | naracteristics                        |  | 1   |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 14  | 80  | -   | -   | V/µs |
| dV <sub>com</sub> /dt | rate of change of commutating voltage | $V_D = 400 \text{ V}; T_j = 110 \text{ °C}; \text{ dI}_{com}/$<br>dt = 0.44 A/ms; gate open circuit                  | 0.5 | -   | -   | V/µs |

**4Q Triac** 



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 9. Normalized gate trigger current as a function of junction temperature

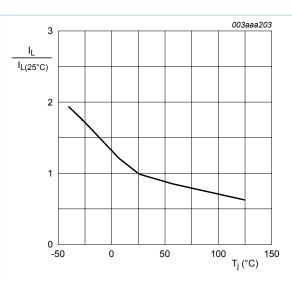


Fig. 10. Normalized latching current as a function of junction temperature

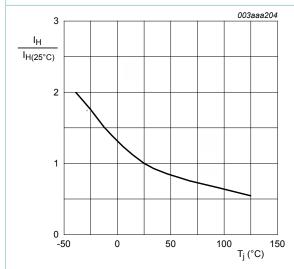
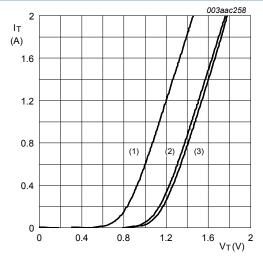


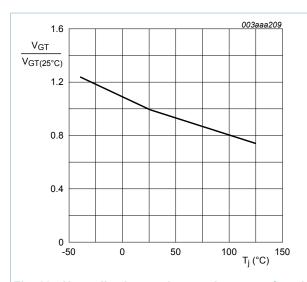
Fig. 11. Normalized holding current as a function of junction temperature



- $V_0 = 1.13 \text{ V}$
- $R_s = 0.31 \Omega$
- (1) T<sub>i</sub> = 125 °C; typical values
- (2) T<sub>i</sub> = 125 °C; maximum values
- (3) T<sub>i</sub> = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

**4Q Triac** 



junction temperature

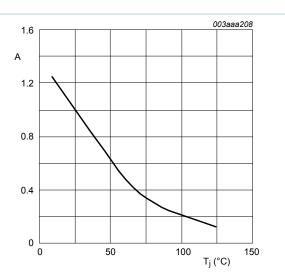
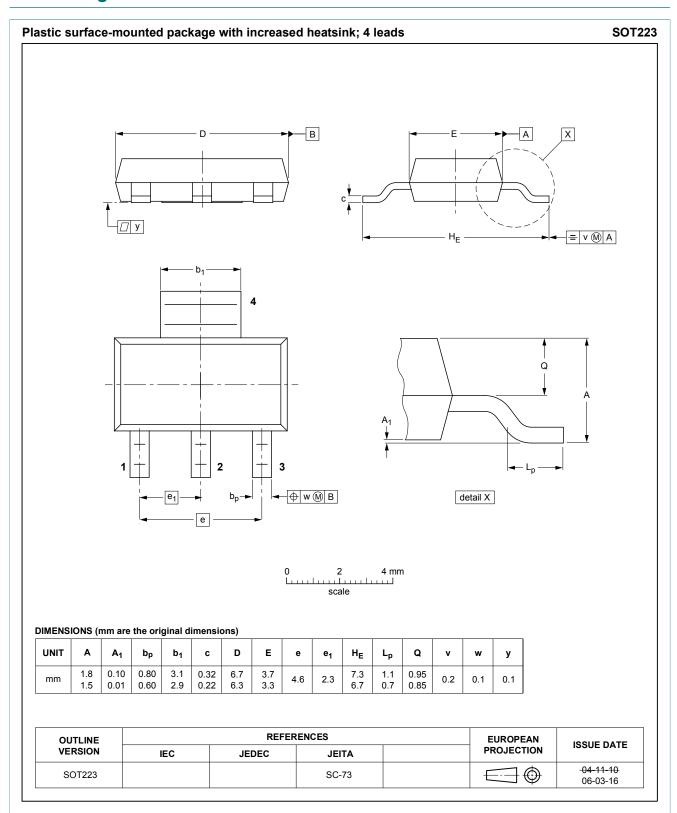


Fig. 13. Normalized gate trigger voltage as a function of Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

$$A = \frac{d\mathrm{V}_{\mathrm{D}(\mathrm{Tj}\,^{\circ}\,\mathrm{C})}\,/\,\,dt}{d\mathrm{V}_{\mathrm{D}(25\,^{\circ}\,\mathrm{C})}/\,\,dt}$$

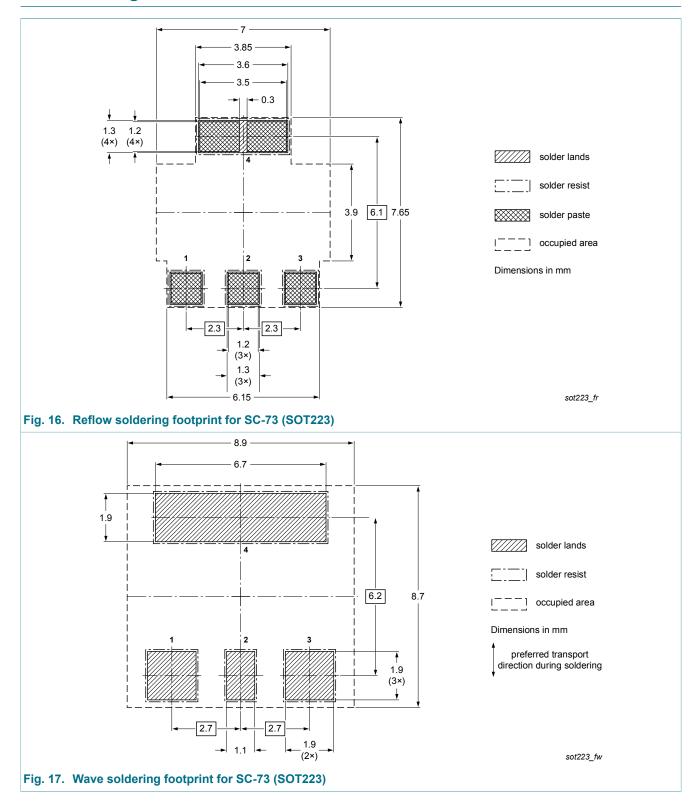
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# 11. Package outline



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# 12. Soldering



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### 13. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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### **4Q Triac**

## 14. Contents

| 1    | General description     | 1  |
|------|-------------------------|----|
| 2    | Features and benefits   | 1  |
| 3    | Applications            | 1  |
| 4    | Quick reference data    | 1  |
| 5    | Pinning information     | 2  |
| 6    | Ordering information    | 2  |
| 7    | Marking                 | 2  |
| 8    | Limiting values         | 3  |
| 9    | Thermal characteristics | 6  |
| 10   | Characteristics         | 8  |
| 11   | Package outline         | 11 |
| 12   | Soldering               | 12 |
| 13   | Legal information       | 13 |
| 13.1 | Data sheet status       | 13 |
| 13.2 | Definitions             | 13 |
| 13.3 | Disclaimers             | 13 |
| 13.4 | Trademarks              | 14 |

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